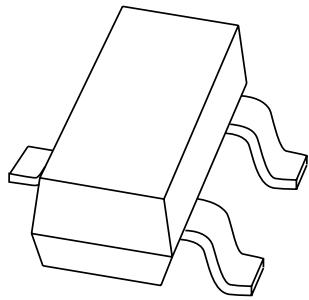


DATA SHEET



BAS16 High-speed diode

Product specification
Supersedes data of 1999 May 26

2001 Oct 10

High-speed diode

BAS16

FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATIONS

- High-speed switching in hybrid thick and thin-film circuits.

DESCRIPTION

The BAS16 is a high-speed switching diode fabricated in planar technology, and encapsulated in a small SOT23 plastic SMD package.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
BAS16	A6*

Note

1. * = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W : Made in China.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	85	V
V_R	continuous reverse voltage		–	75	V
I_F	continuous forward current	see Fig.2; note 1	–	215	mA
I_{FRM}	repetitive peak forward current		–	500	mA
I_{FSM}	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4 $t = 1\ \mu\text{s}$ $t = 1\ \text{ms}$ $t = 1\ \text{s}$	–	4 1 0.5	A A A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

PINNING

PIN	DESCRIPTION
1	anode
2	not connected
3	cathode

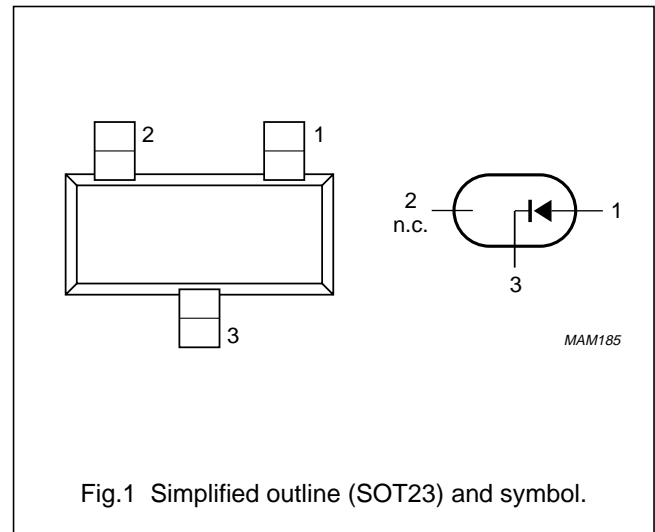


Fig.1 Simplified outline (SOT23) and symbol.

High-speed diode

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ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_F	forward voltage	see Fig.3		
		$I_F = 1\text{ mA}$	715	mV
		$I_F = 10\text{ mA}$	855	mV
		$I_F = 50\text{ mA}$	1	V
I_R	reverse current	see Fig.5		
		$V_R = 25\text{ V}$	30	nA
		$V_R = 75\text{ V}$	1	μA
		$V_R = 25\text{ V}; T_j = 150\text{ °C}$	30	μA
		$V_R = 75\text{ V}; T_j = 150\text{ °C}$	50	μA
C_d	diode capacitance	$f = 1\text{ MHz}; V_R = 0$; see Fig.6	1.5	pF
t_{rr}	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}; R_L = 100\ \Omega$; measured at $I_R = 1\text{ mA}$; see Fig.7	4	ns
V_{fr}	forward recovery voltage	when switched from $I_F = 10\text{ mA}; t_r = 20\text{ ns}$; see Fig.8	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		330	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

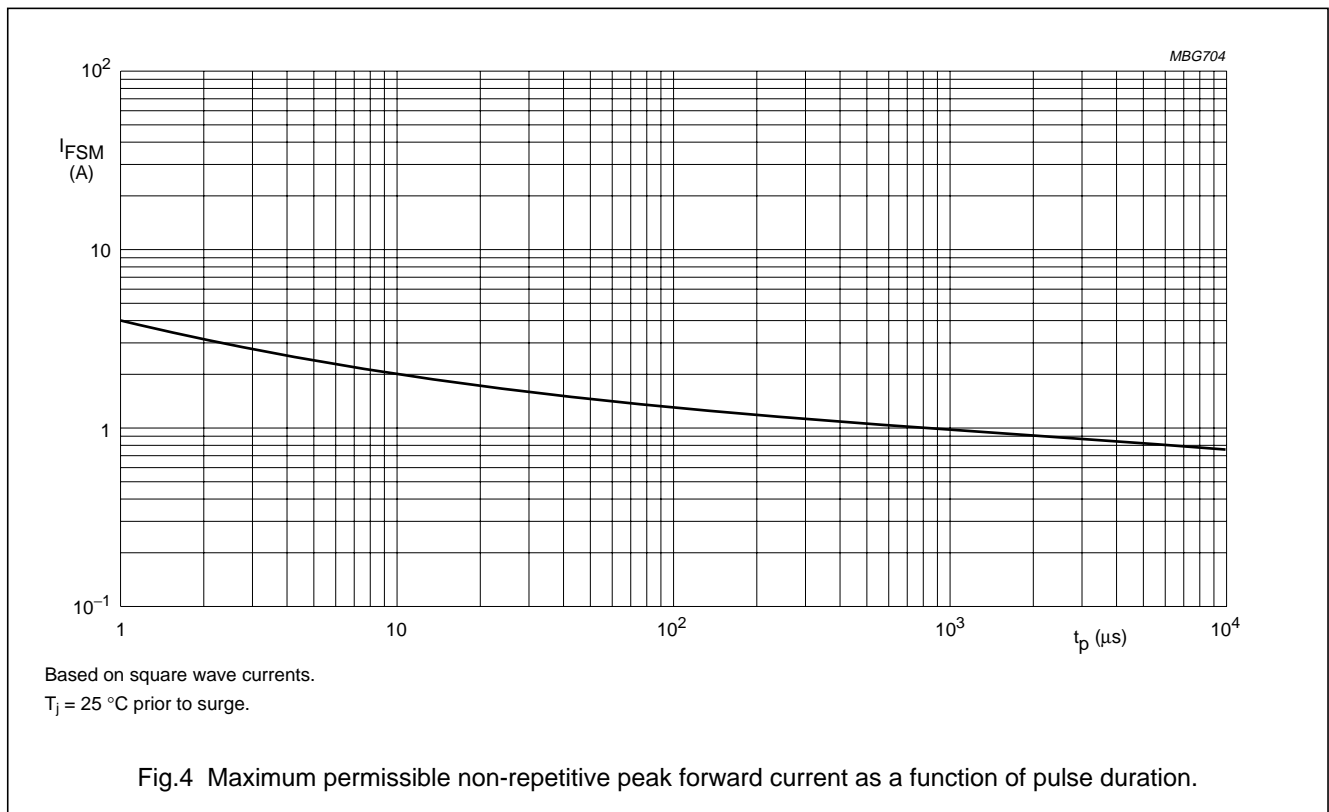
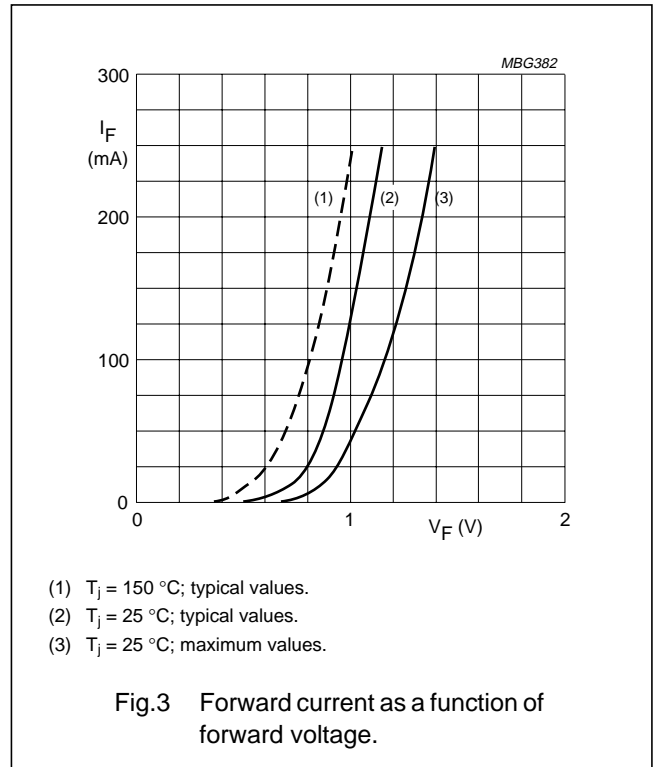
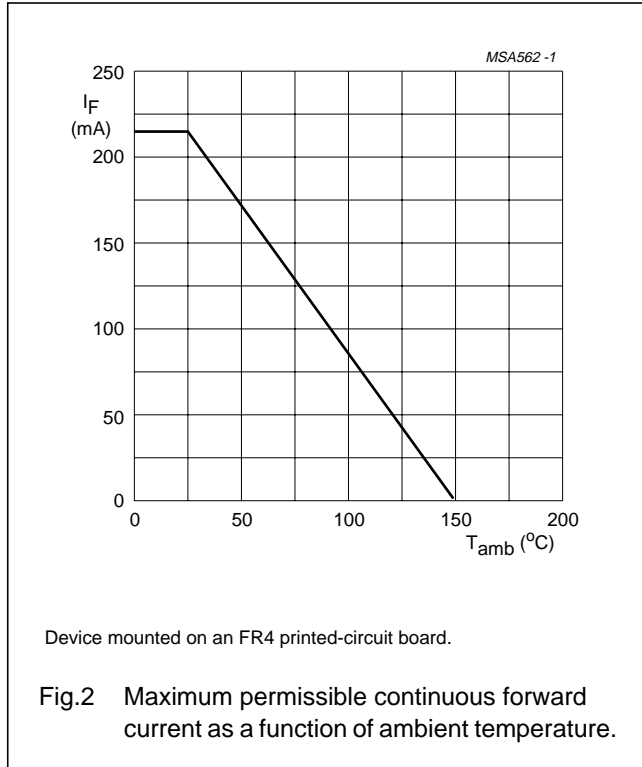
Note

1. Device mounted on an FR4 printed-circuit board.

High-speed diode

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GRAPHICAL DATA



High-speed diode

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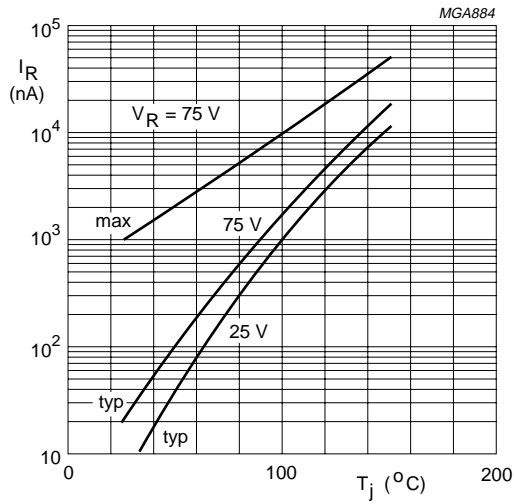
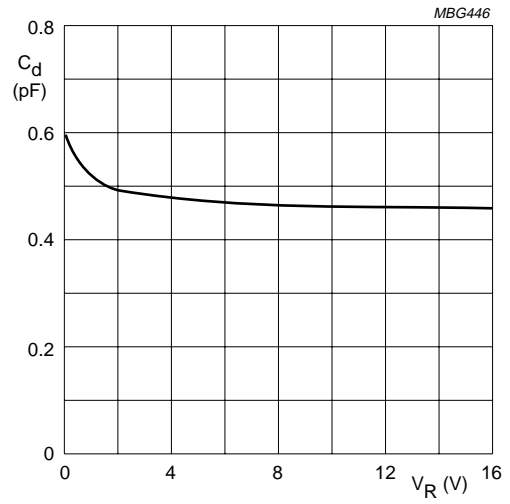


Fig.5 Reverse current as a function of junction temperature.

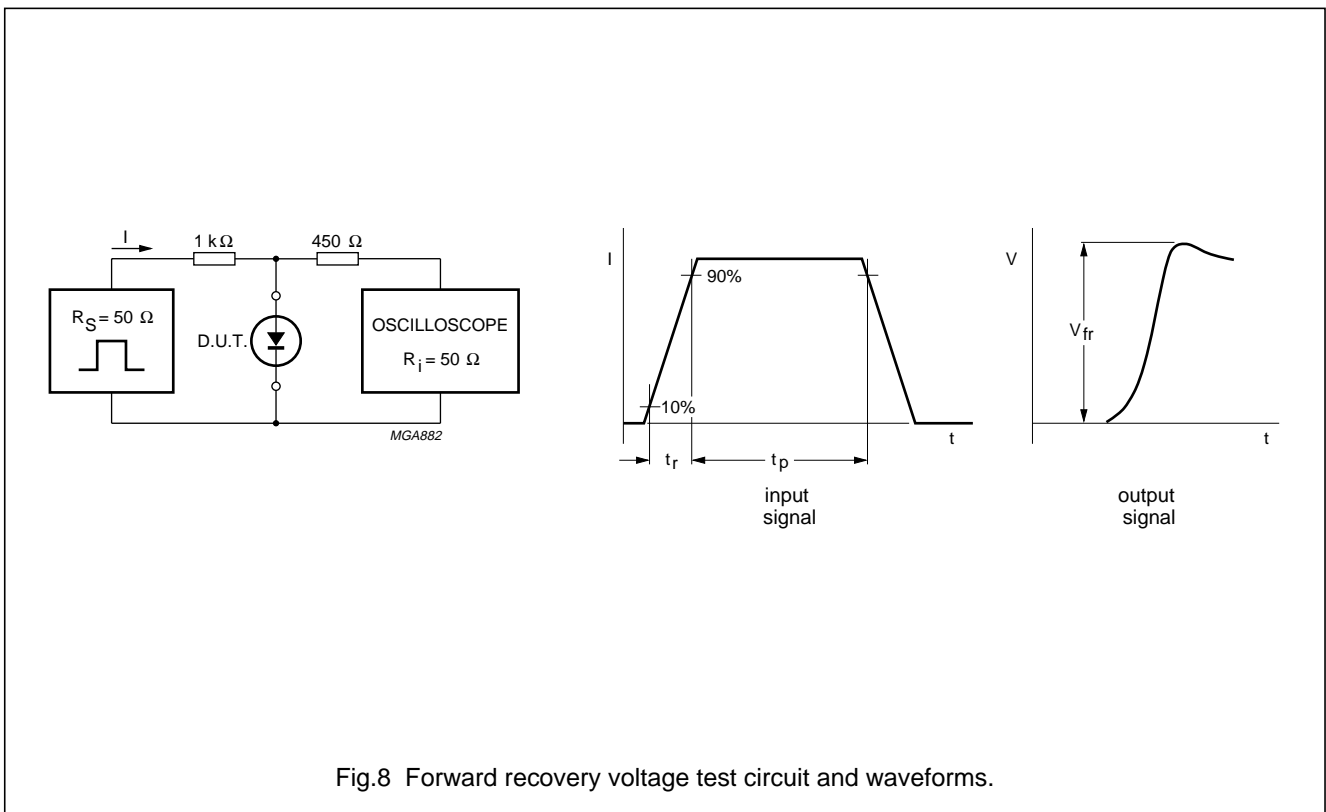
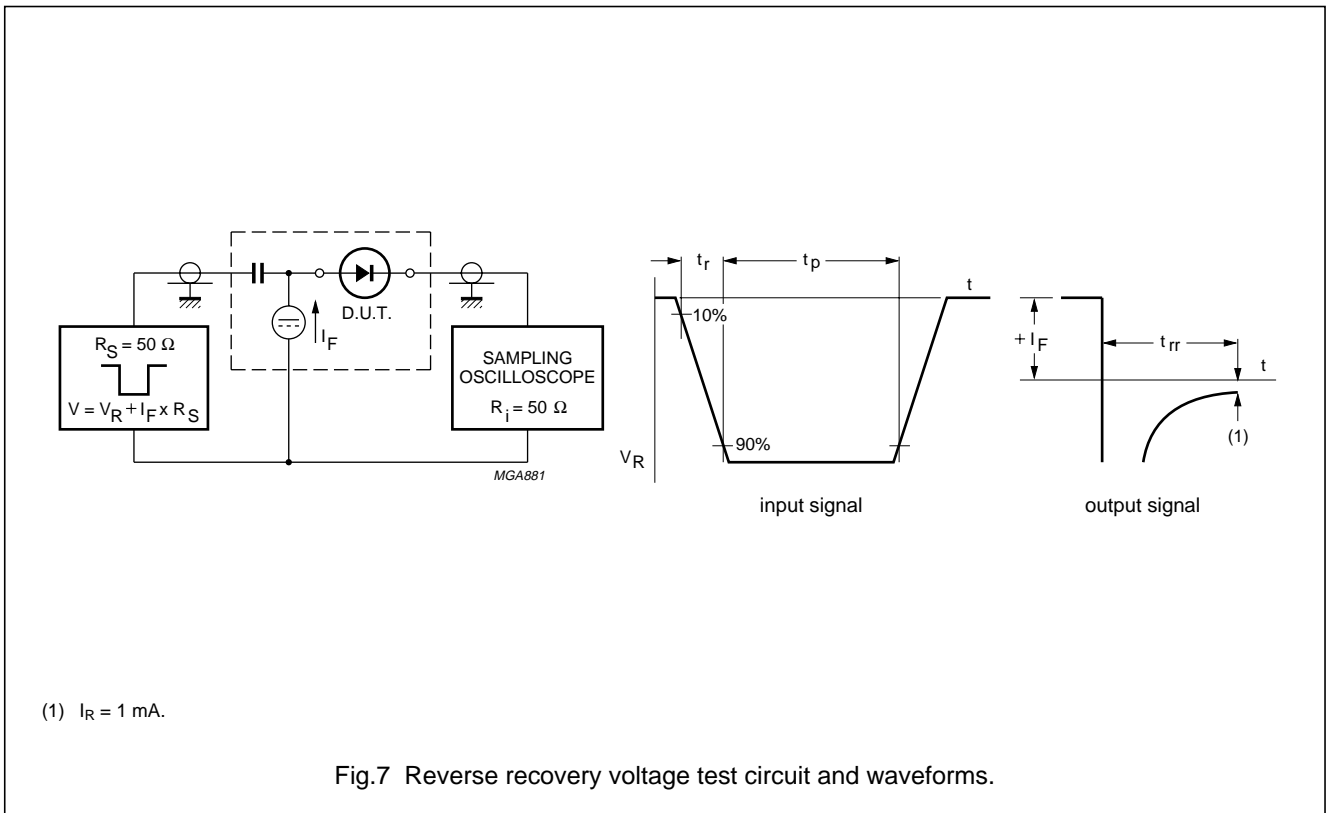


$f = 1$ MHz; $T_j = 25$ °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

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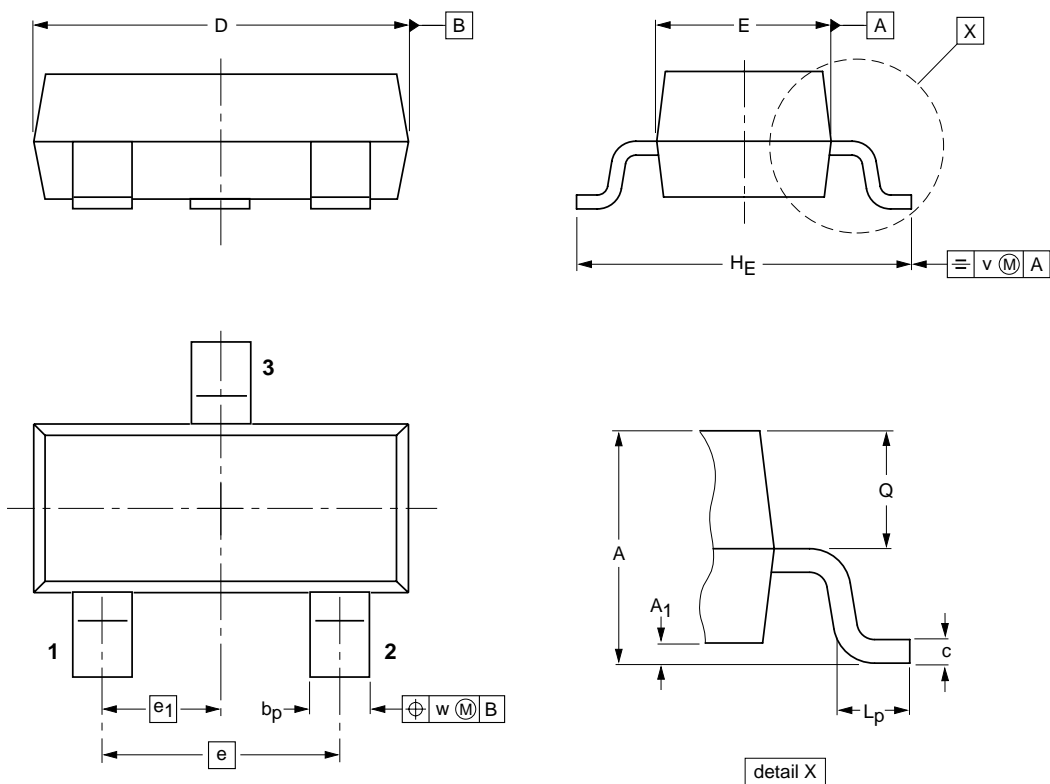
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT23		TO-236AB			97-02-28 99-09-13

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DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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High-speed diode

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NOTES

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